

COMPLIANT

4 Ω , 360 MHz, Dual SPST Analog Switches

DESCRIPTION

The DG3537, DG3538, DG3539, DG3540 are dual SPST analog switches which operate from 1.8 V to 5.5 V single rail power supply. They are design for audio, video, and USB switching applications.

The devices have 4 Ω on-resistance and 360 MHz 3 dB bandwidth. 0.2 Ω on-resistance matching and 1 Ω flatness make the device high linearity. The devices are 1.6 V logic compatible within the full operation voltage range.

These switches are built on a sub-micron high density process that brings low power consumption and low voltage performance.

The switches are packaged in MICRO FOOT chip scale package of 3 x 3 bump array.

As a committed partner to the community and environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switch products manufactured with tin/silver/copper (SnAgCu) device termination, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- 1.8 V to 5.5 V operation
- 3 Ω at 2.7 V R_{ON}
- 360 MHz 3 dB bandwidth
- ESD method 3015.7 > 2 kV
- Latch-up current 0.300 mA (JESD 78)
- 1.6 V logic compatible

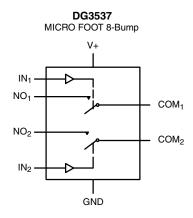
BENEFITS

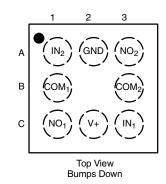
- Space saving MICRO FOOT[®] package
- High linearity
- · Low power consumption
- · High bandwidth
- · Full rail Signal swing range

APPLICATIONS

- · Cellular phones
- MP3
- Media players
- Modems
- Hard drives
- PCMCIA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION







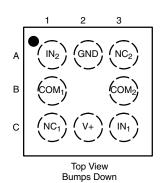
3537 = Device Marking xxx = Data/Lot Traceability Code

Document Number: 73320 S11-0303-Rev. D, 28-Feb-11



FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG3538 MICRO FOOT 8-Bump V+ IN1 NC1 NC2 IN2 GND



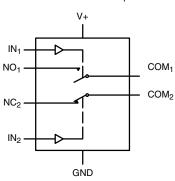


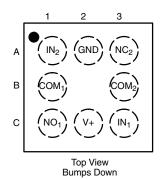


3538 = Device Marking

xxx = Data/Lot Traceability Code







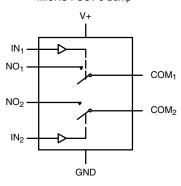
Device Marking

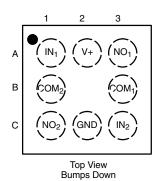


3539 = Device Marking

xxx = Data/Lot Traceability Code

DG3540 MICRO FOOT 8-Bump





Device Marking



3540 = Device Marking

xxx = Data/Lot Traceability Code

TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION							
Temp. Range	Package	Part Number					
- 40 °C to 85 °C	MICRO FOOT: 8 Bump (3 x 3, 0.5 mm Pitch, 238 μm Bump Height)	DG3537DB-T5-E1 DG3538DB-T5-E1 DG3539DB-T5-E1 DG3540DB-T1-E1					





ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference V+ to GND	- 0.3 to + 6					
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3 V)	V				
Continuous Current (NO, NC, COM)	± 100	mA				
Peak Current (Pulsed at 1 ms, 10 % duty	± 200	IIIA				
Storage Temperature	(D Suffix)	- 65 to 150				
Package Solder Reflow Conditions ^b	IR/Convection	250	°C			
ESD per Method 3015.7	•	> 2	kV			
Power Dissipation (Packages) ^c	MICRO FOOT: 8 Bump (3 x 3 mm) ^d	400	mW			

Notes

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. Refer to IPC/JEDEC (J-STD-020B)
- c. All bumps welded or soldered to PC Board.
- d. Derate 5.0 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V+ = 2.7 \text{ to } 3.6 \text{ V}, V_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^e$	Temp.a	Min.b	Typ.c	Max.b	Unit
Analog Switch							
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
On-Resistance ^d	R _{ON}		Room Full		3	4 4.3	
R _{ON} Flatness ^d	R _{ON} Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 0.2/1.5 \text{ V}$ $I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.75	1.2	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		Room			0.25	
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 3.6 V,	Room Full	- 2 - 20		2 20	
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 0.3 \text{ V}/3.3 \text{ V}$, $V_{COM} = 3.3 \text{ V}/0.3 \text{ V}$	Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.6 V, $V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V}/3.3 \text{ V}$	Room Full	- 2 - 20		2 20	
Digital Control	•						,
Input High Voltage ^d	V _{INH}		Full	1.4			V
Input Low Voltage	V _{INL}		Full			0.5]
Input Capacitance	C _{in}		Full		8		pF
Input Current ^f	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μΑ

DG3537, DG3538, DG3539, DG3540

Vishay Siliconix



SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		_		Limits 0 °C to 85 °C	
Parameter	Symbol	$V+ = 2.7 \text{ to } 3.6 \text{ V}, V_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^e$	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 2.7 V, V _{NO} or V _{NC} = 1.5 V	Room Full		16	46 48	ns
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega$, $C_L = 35 pF$	Room Full		7	37 39	115
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 2 V, R_{GEN} = 0 Ω	Room		1		рC
Off-Isolation ^d	OIRR	D 5000 5 5 5 1 1 MHz	Room		- 78.5		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 113		dB
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 10 MHz$	Room		- 58		иь
Crosstalk ^d	X _{TALK}	$n_L = 50 \Omega_s$, $G_L = 5 \text{ pr}$, $T = 10 \text{ N/mz}$	Room		- 66		
O" Otd	C _{NO/NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		8		
Off Capacitance ^d	C _{COM(off)}		Room		14		pF
Observation Constitution of	C _{NO/NC(on)}	VIN - 0 01 V+, 1 - 1 WILL	Room		27		Pi
Channel-On Capacitance ^d	C _{COM(on)}		Room		27		
Power Supply				•			
Power Supply Current	l+	$V_{IN} = 0$ or $V+$	Room Full		0.001	1.0 1.0	μΑ



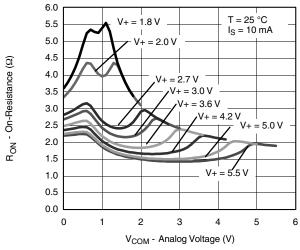
SPECIFICATIONS (V+ = 5 V)								
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C				
Parameter	Symbol	V+ = 4.2 to 5.5 V, V_{IN} = 0.8 V or 2.0 V^e	Temp.a	Min.b	Typ.c	Max.b	Unit	
Analog Switch								
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V	
On-Resistance ^d	R _{ON}		Room Full		2.6	3.5 3.7		
r _{ON} Flatness ^d	R _{ON} Flatness	$V+ = 4.2 \text{ V}, V_{COM} = 0.5/3.5 \text{ V}$ $I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.8	1.2	Ω	
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		Room			0.2		
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V,	Room Full	- 2 - 20		2 20		
Switch On Leakage Current	I _{COM(off)}		Room Full	- 2 - 20		2 20	nA	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 5.5 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 1.0 \text{ V}/4.5 \text{ V}$	Room Full	- 2 - 20		2 20		
Digital Control								
Input High Voltage ^d	V _{INH}		Full	2.0			v	
Input Low Voltage	V_{INL}		Full			0.8	•	
Input Capacitance	C _{in}		Full		8		pF	
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$ or $V+$	Full	1		1	μΑ	
Dynamic Characteristics							,	
Turn-On Time	t _{ON}	$V + = 4.2 \text{ V}, V_{NO} \text{ or } V_{NC} = 3.0 \text{ V}$	Room Full		11	41 43	ns	
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega$, $C_L = 35 pF$	Room Full		7	37 39	110	
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 2 V, R_{GEN} = 0 Ω	Room		1		рC	
Off Capacitance ^d	C _{NO/NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		8			
	C _{COM(off)}		Room		14		pF	
Channel-On Capacitanced	C _{NO/NC(on)}	VIIV - 0 01 VT, 1 - 1 WII 12	Room		28		ρι	
·	C _{COM(on)}				28			
Power Supply				r	1			
Power Supply Current	I+	$V_{IN} = 0$ or V+	Room Full		0.001	1.0 1.0	μΑ	

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

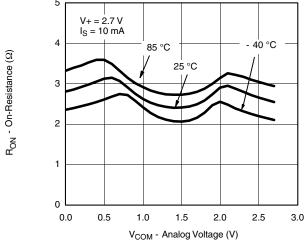
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

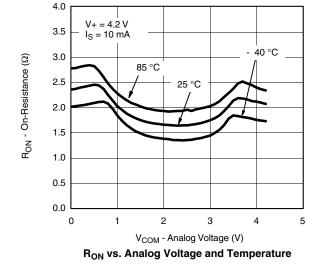


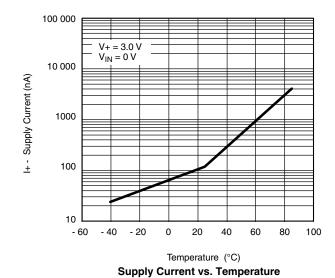
 $R_{\mbox{\scriptsize ON}}$ vs. $V_{\mbox{\scriptsize COM}}$ and Supply Voltage

10 mA



R_{ON} vs. Analog Voltage and Temperature





1 mA V+=3V

100 μA

10 μA

10 μA

1 μA

100 nA

1 nA

1 nA

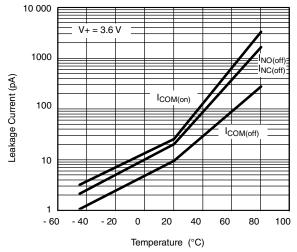
100 pA

1

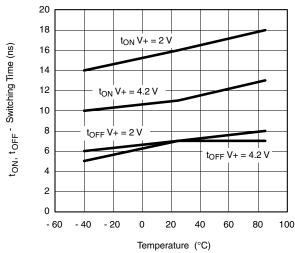
Supply Current vs. Input Switching Frequency



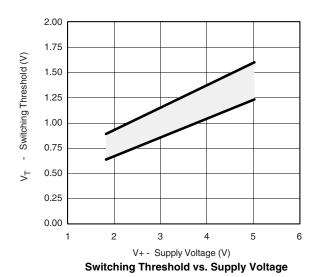
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



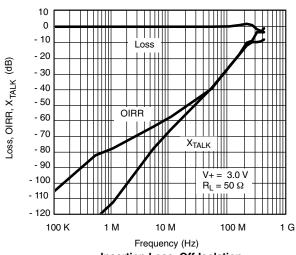
Leakage Current vs. Temperature



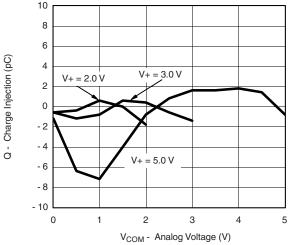
Switching Time vs. Temperature



300 250 V + = 3.6 V200 150 I_{NO(off)}, I_{NC(off)} Leakage Current (pA) 100 I_{COM(off)} 50 0 I_{COM(on)} - 50 - 100 - 150 - 200 - 250 - 300 0.0 0.5 2.0 3.5 4.0 1.0 1.5 2.5 3.0 V_{COM}, V_{NO}, V_{NC} - Analog Voltage (V) Leakage vs. Analog Voltage



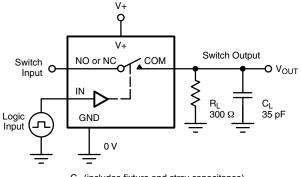
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Charge Injection vs. Analog Voltage

TEST CIRCUITS





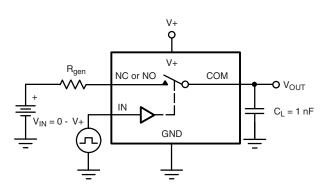
Logic Input V_{INH} V_{INL} V_{INL} $t_r < 5 \text{ ns}$ $t_f < 5 \text{ ns}$

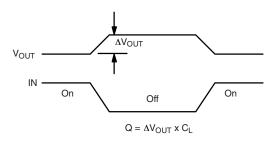
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{NOorNC} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

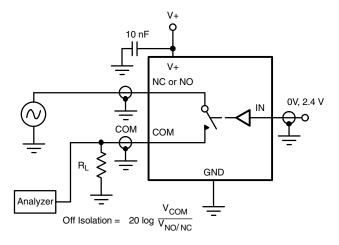
Figure 1. Switching Time





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 2. Charge Injection



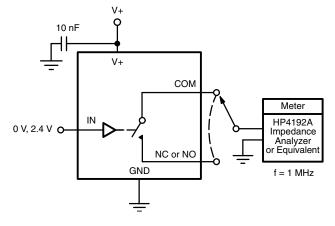


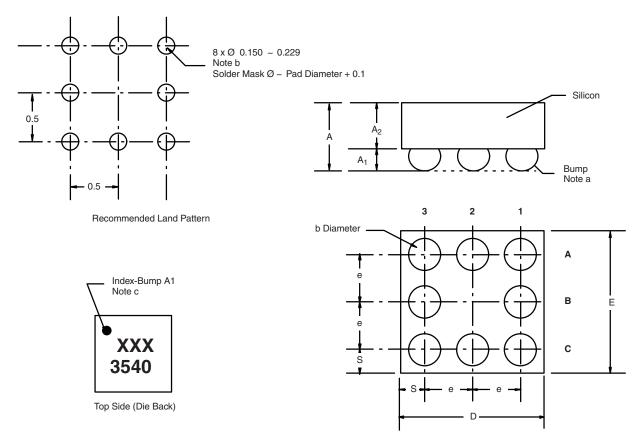
Figure 3. Off-Isolation

Figure 4. Channel Off/On Capacitance



PACKAGE OUTLINE

MICRO FOOT: 8 BUMP (3 x 3, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

- a. Bump is Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

	Millimeters ^a		Inc	hes
Dim.	Min.	Max.	Min.	Max.
A	0.688	0.753	0.0271	0.0296
A ₁	0.218	0.258	0.0086	0.0102
A ₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.480	1.520	0.0583	0.0598
E	1.480	1.520	0.0583	0.0598
е	0.5 B	ASIC	0.0197 BASIC	
S	0.230	0.270	0.0091	0.0106

Notes

a. Use millimeters as the primary measurement.

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